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UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY LTD.
Petitioner

v.

GODO KAISHA IP BRIDGE 1
Patent Owner.

Case IPR2017-01844

PETITIONER'S UPDATED EXHIBIT LIST



U.S. Patent 7,893,501 IPR2017-01844 Petitioner's Updated Exhibit List

Pursuant to the Board's Order dated December 29, 2017, Petitioner hereby submits the December 19, 2017 Conference Call Transcript as Exhibit 1334 and the infringement contentions dated February 1, 2017 for U.S. Patent 7,893,501 from *Godo Kaisha IP Bridge 1 v. Xilinx, Inc.*, Case No. 2:17-cv-00100 (E.D. Tex.) as Exhibit 1335. Petitioner also hereby submits an updated exhibit list.

Respectfully Submitted,

/ Michael Smith/

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CERTIFICATE OF SERVICE

I hereby certify that, on January 9, 2018, I caused a true and correct copy of the foregoing materials:

- Petitioner's Updated Exhibit List
- Petitioner's List of Exhibits
- Exhibits 1334 and 1335

to be served via email on the following counsel of record as listed in Patent Owner's Mandatory Notices:

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> > Respectfully Submitted,

/ Michael Smith/

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<u>PETITIONER'S LIST OF EXHIBITS FOR</u> <u>IPR2017-01844</u>

Exhibit	Description
1301	U.S. Patent No. 7,893,501
1302	Declaration of Stanley R. Shanfield, Ph.D. Regarding U.S. Patent No. 7,893,501, Claims 6, 12, 13, 19 and 21 ("Shanfield Decl.")
1303	Applicant's Amendment and Response dated August 6, 2010
1304	U.S. Patent No. 5,960,270 to Misra et al. ("Misra")
1305	U.S. Patent No. 5,472,890 to Oda ("Oda")
1306	U.S. Patent Publication No. 2002/0000611 to Hokazono et al. ("Hokazono")
1307	U.S. Patent Publication No. 2002/0145156 to Igarashi et al. ("Igarashi")
1308	U.S. Patent No. 6,072,237 to Jang et al. ("Jang")
1309	J. Plummer et al., <i>Silicon VLSI Technology: Fundamentals</i> , <i>Practice, and Modeling</i> , (1 st ed. 2000)
1310	K. Maex et al, <i>Simply irresistible silicides</i> , Physics World, at 35-39 (Nov. 1995)
1311	J. Rabaey et al., <i>Digital Integrated Circuits</i> , at 40-44 (2d ed. 2003) ("Rabaey")
1312	U.S. Patent Application No. 2003/0011043 ("Roberts")
1313	U.S. Patent No. 4,951,100 ("Parrillo")
1314	U.S. Patent No. 6,110,827 to Chien et al. ("Chien")
1315	U.S. Patent No. 6,444,566 to Tsai et al. ("Tsai")



Exhibit	Description
1316	Togo, M. et al. "Low Leakage and High Reliability 1.5 nm SiON Gate-Dielectric Using Radical Oxynitridation for Sub-0.1 µm CMOS," 2000 Symposium on VLSI Technology Digest of Technical Papers (2000) ("Togo")
1317	U.S. Patent No. 6,228,777 ("Arafa")
1318	U.S. Patent No. 6,509,234
1319	U.S. Patent No. 5,726,479
1320	U.S. Patent No. 6,512,266
1321	U.S. Patent No. 6,806,584
1322	J. Moon et al., A New LDD Structure: Total Overlap with Polysilicon Spacer (TOPS), IEEE Electron Device Letters, Vol. 11, No. 5, at 221-223 (May 1990)
1323	D. Baglee et al., Reduced Hot-Electron Effects in MOSFET's with an Optimized LDD Structure, IEEE Electron Device Letters, Vol. EDL-5, No. 10, at 389-391 (Oct. 1984)
1324	U.S. Patent No. 6,383,906 to Wieczorek et al. ("Wieczorek")
1325	K.B. Sundaram et al., Fabrication of Metal Field Effect Transistors Using Silicon Nitride and Silicon-Oxynitride as Gate Insulators, Electrochemical Proceedings, vol. 97-10 (1997) ("Sundaram")
1326	Kastenmeier et al., "Remote plasma etching of silicon nitride and silicon dioxide using NF ₃ /O ₂ gas mixtures," J. Vac. Sci. Technol. A 16(4), Jul/Aug 1998 ("Kastenmeier")
1327	High k dielectrics – Current status and Materials Properties Considerations, Wilk, G.D., et al., J. App. Phy. Vol. 89, No. 10, May 15, 2001



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